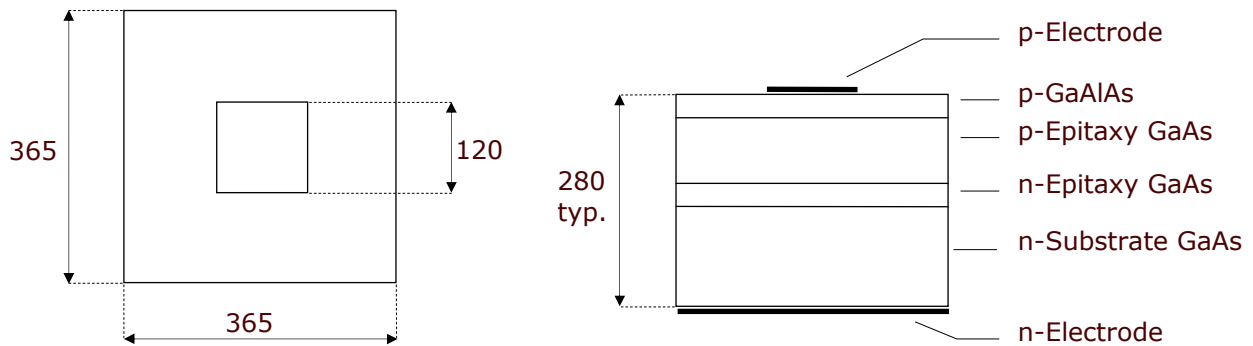


INFRA-RED

Item No.: 131234

1. This specification applies to GaAs / GaAs LED Chips with GaAlAs window - layer
2. Structure
 - 2.1 Mesa structure
 - 2.2 Electrodes

| | |
|------------------|----------|
| p-side (anode) | Au alloy |
| n-side (cathode) | Au alloy |
3. Outlines (dimensions in microns)



Wire bond contacts can also have a spider shape

4. Electrical and optical characteristics (T=25°C)

| Parameter | Symbol | Conditions | min | typ | max | Unit |
|-----------------|-------------|-----------------------|-----|------|------|---------------|
| Forward voltage | V_F | $I_F = 20 \text{ mA}$ | | 1,20 | 1,40 | V |
| Reverse current | I_R | $I_R = 5 \text{ V}$ | | | 10 | μA |
| output Power * | Φ_e | $I_F = 20 \text{ mA}$ | 2,0 | 2,4 | | mW |
| | | $I_F = 50 \text{ mA}$ | 5,0 | 6,0 | | |
| Switching time | t_r, t_f | $I_F = 20 \text{ mA}$ | | 500 | | ns |
| Peak wavelength | λ_p | $I_F = 20 \text{ mA}$ | | 950 | | nm |

* On request, wafers will be delivered according to output power classes
Power measurement at OSA on gold plate

5. Packing
 - 1) wire bond side on top
 - 2) back contact on top

6. Labeling

| Type | Lot No. | Φ_e typ min max | Quantity |
|------|---------|----------------------------|----------|
|------|---------|----------------------------|----------|